

IN THE SPECIFICATION:

Please amend the Abstract, on page 25 of the specification, between lines 4 and 13, as follows:

An asymmetric-area memory cell, and a fabrication method for forming an asymmetric-area memory cell, are provided. The method includes ~~comprises~~: forming a bottom electrode having an area; forming a CMR memory film overlying the bottom electrode, having an asymmetric area; and, forming a top electrode having an area, less than the bottom electrode area, overlying the CMR film. In one aspect, the CMR film has a first area adjacent the top electrode and a second area, greater than the first area, adjacent the bottom electrode. Typically, the CMR film first area is approximately equal to the top electrode area, although the CMR film second area may be less than the bottom electrode area.